

ABSTRACT OF THE DISCLOSURE

A semiconductor device which is here disclosed includes a first wiring layer having a first lower end and a first upper end protruded more than the first  
5 lower end, and a second wiring layer having a second lower end and a second upper end protruded more than the second lower end, the second upper end facing the first upper end with the interposition of a first gap, and the second lower end facing the first lower end  
10 with the interposition of a second gap larger than the first gap.